

# UT54ACS162245SLV

## Features

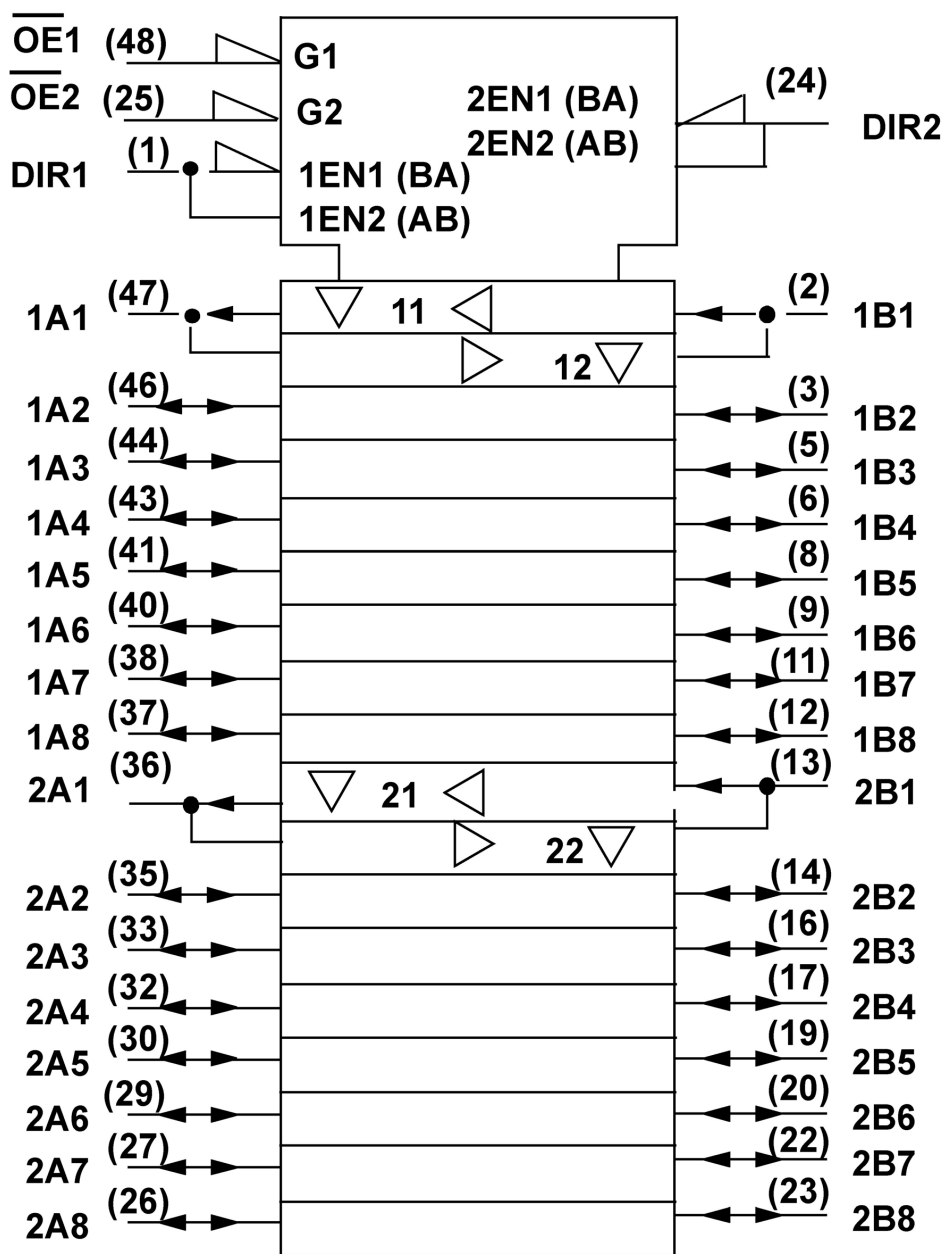
- Voltage translation
  - 3.3V bus to 2.5V bus
  - 2.5V bus to 3.3V bus
- Cold sparing all pins
- 0.25 $\mu$  CMOS
- Operational environment
  - Total dose: 300Krad(Si) and 1Mrad(Si)
  - Single Event Latchup immune
- High speed, low power consumption
- Schmitt trigger inputs to filter noisy signals
- Cold and Warm Spare - all outputs
- Available QML Q or V processes
- Standard Microcircuit Drawing 5962-02543
- Package:
  - 48-lead flatpack, 25 mil pitch (.390 x .640), wgt 1.4 Grams

## Description

The 16-bit wide UT54ACS162245SLV MultiPurpose low voltage transceiver is built using CAES epitaxial CMOS technology and is ideal for space applications. This high speed, low power UT54ACS162245SLV low voltage transceiver is designed to perform multiple functions including: asynchronous two-way communication, Schmitt input buffering, voltage translation, warm and cold sparing. With  $V_{DD}$  equal to zero volts, the UT54ACS162245SLV outputs and inputs present a minimum impedance of  $1M\Omega$  making it ideal for "cold spare" applications. Balanced outputs and low "on" output impedance make the UT54ACS162245SLV well suited for driving high capacitance loads and low impedance backplanes. The UT54ACS162245SLV enables system designers to interface 2.5 volt CMOS compatible components with 3.3 volt CMOS components. For voltage translation, the A port interfaces with the 2.5 volt bus; the B port interfaces with the 3.3 volt bus. The direction control (DIRx) controls the direction of data flow. The output enable ( $\overline{OEx}$ ) overrides the direction control and disables both ports. These signals can be driven from either port A or B. The direction and output enable controls operate these devices as either two independent 8-bit transceivers or one 16-bit transceiver.

# UT54ACS162245SLV

## Logic Symbol

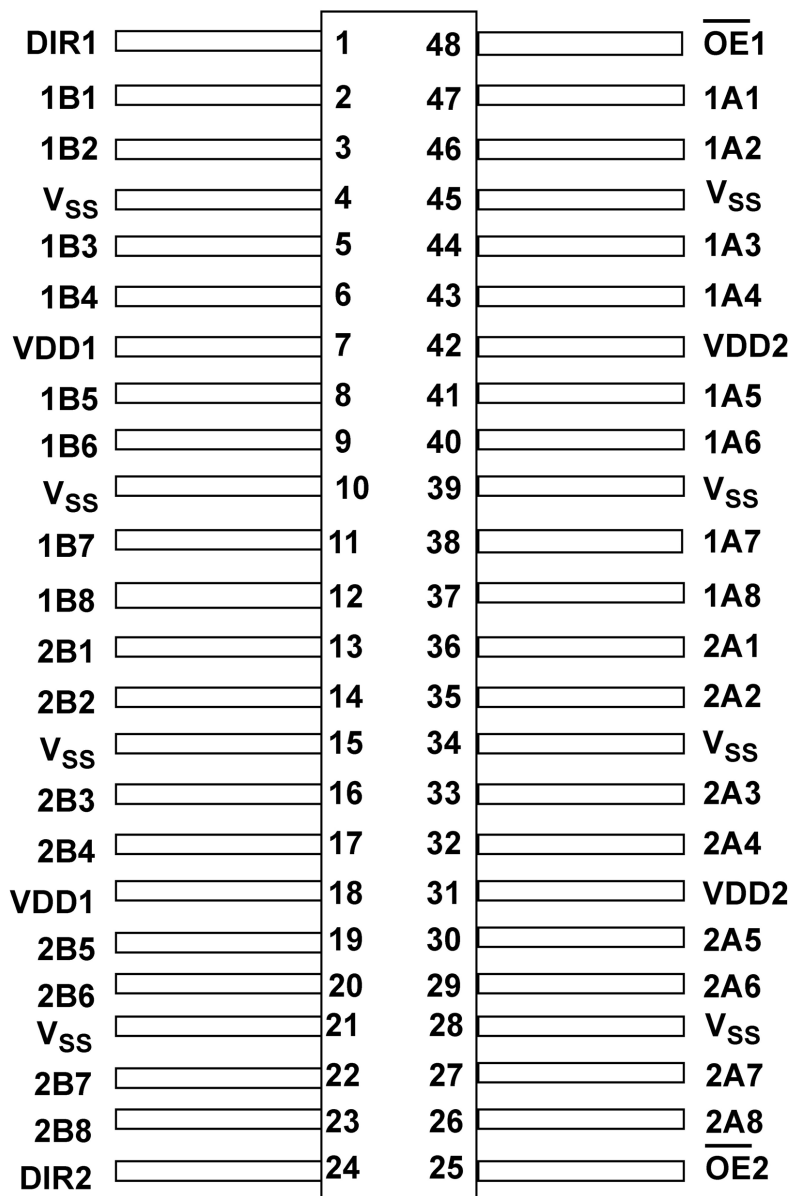


## Pin Description

Pin Names	Description
$\overline{OE}x$	Output Enable Input (Active Low)
DIRx	Direction Control Inputs
xAx	Side A Inputs or 3-State Outputs (2.5V Port)
xBx	Side B Inputs or 3-State Outputs (3.3V Port)

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## Pinouts



48-Lead Flatpack  
Top View

## Power Table

Port B	Port A	Operation
3.3 Volts	2.5 Volts	Voltage Translator
3.3 Volts	3.3 Volts	Non Translating
2.5 Volts	2.5 Volts	Non Translating

# UT54ACS162245SLV

## Function Table

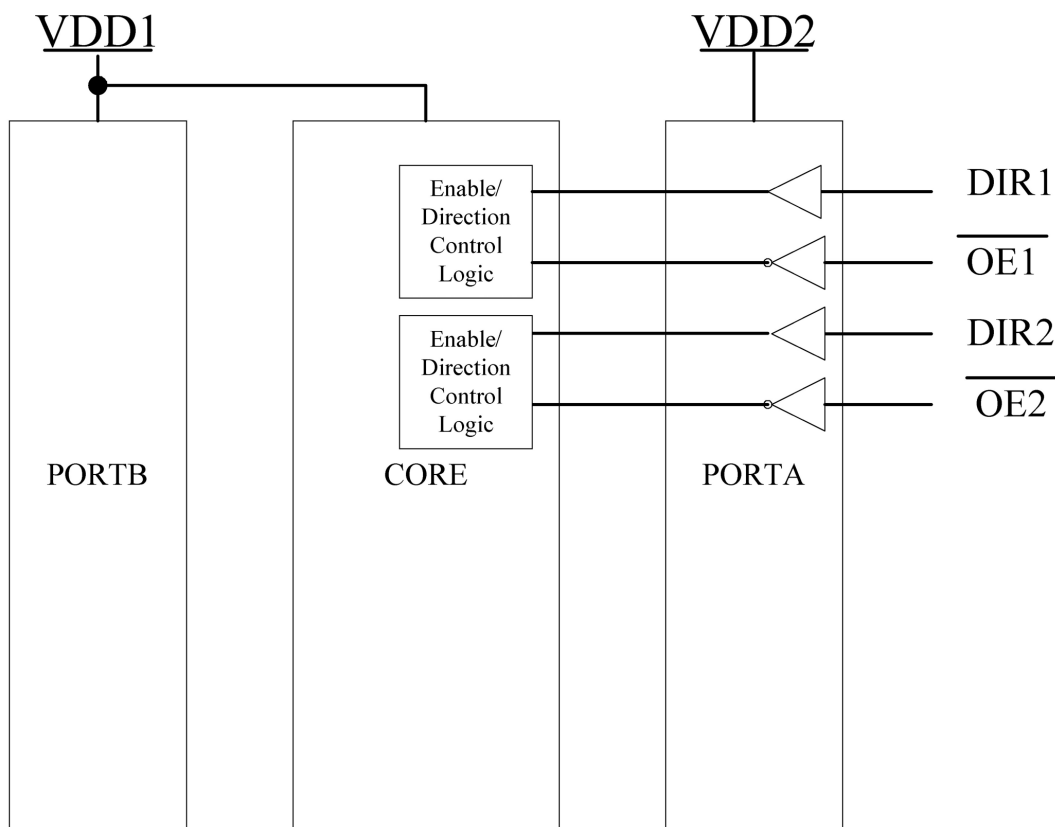
Enable $\overline{OE}_x$	Direction DIR $_x$	Operation
L	L	B Data to A Bus
L	H	A Data to B Bus
H	X	Isolation

## Power Application Guidelines

For proper operation, connect power to all  $V_{DD}$  pins and ground all  $V_{SS}$  pins (i.e., no floating  $V_{DD}$  or  $V_{SS}$  supply pins). If  $V_{DD1}$  and  $V_{DD2}$  are not powered up together, then  $V_{DD2}$  should be powered up first to ensure proper control of output enable ( $\overline{OE}_x$ ) and direction control (DIR $_x$ ). Control of the outputs /  $\overline{OE}_x$  and DIR $_x$  pins is not guaranteed until  $V_{DD2}$  reaches 1.5 +/-5%. During normal operation of the device, after power up, insure  $V_{DD1} \geq V_{DD2}$ .

## Power Up Sequence

Users should power up  $V_{DD2}$  before  $V_{DD1}$  because the DIR $_x$  and  $\overline{OE}_x$  pins on the UT54ACS162245SLV are powered by  $V_{DD2}$ . If  $V_{DD1}$  is powered on first,  $V_{DD2}$  must be powered on within 1 second of  $V_{DD1}$  reaching 1.5V +/-5%. An elevated  $V_{DD1}$  supply current up to 150mA may occur when  $V_{DD1} > 1.5V + 5\%$  and  $V_{DD2} < 1.5V +/-5\%$ .



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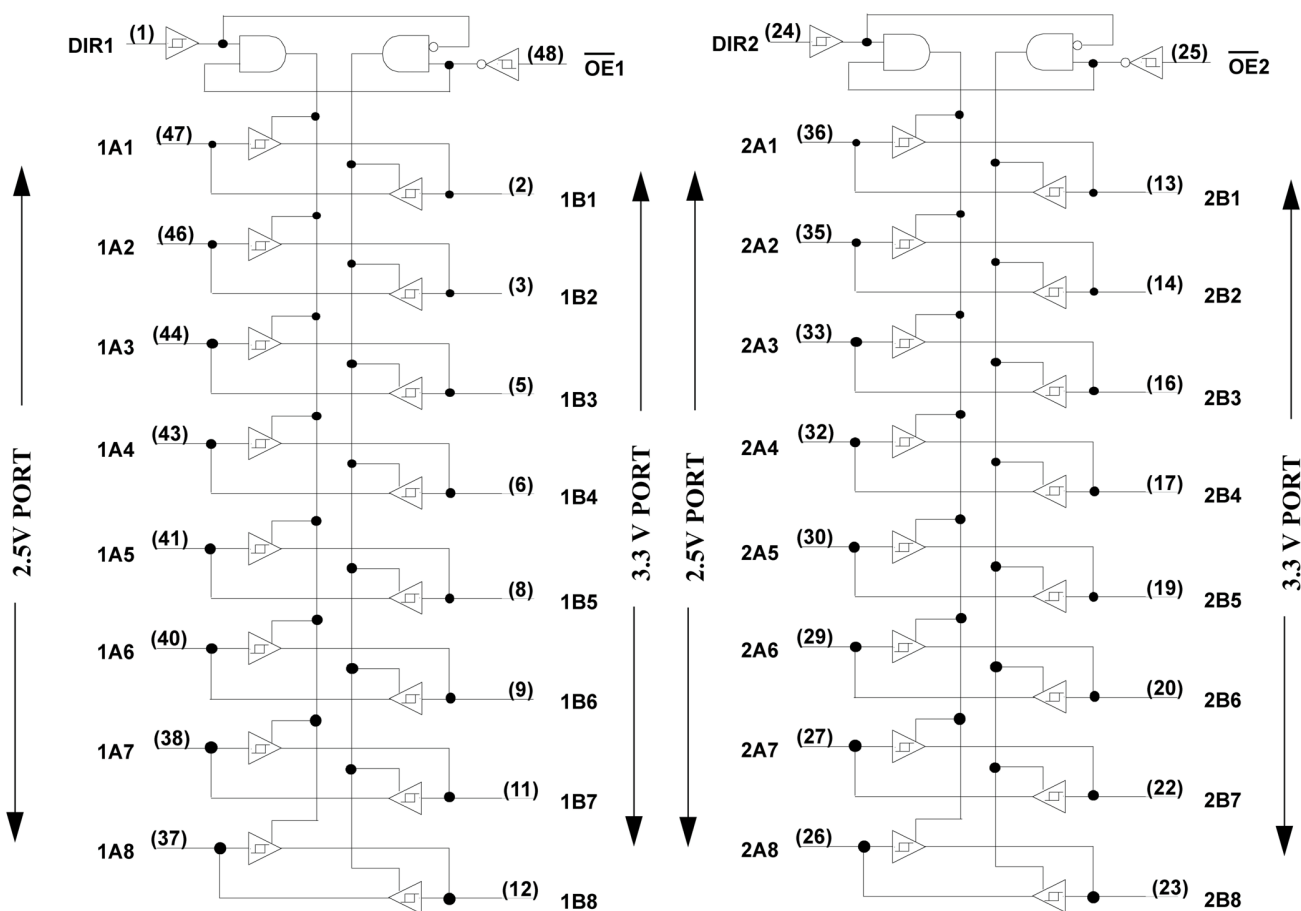
## Warm Spare

Once the UT54ACS162245SLV is powered up with  $V_{DD1} \geq V_{DD2}$ , the application may place the device into "Warm Spare" mode by driving EITHER supply to  $V_{SS} \pm 0.25V$  with a maximum  $1k\Omega$  impedance between  $V_{DDX}$  and  $V_{SS}$ . While in Warm Spare, the device places all outputs into a high impedance state (see DC electrical parameters,  $I_{ws}$ ).

## Cold Spare

The UT54ACS162245SLV places the device into "Cold Spare" mode when BOTH supplies are set to  $V_{SS} \pm 0.25V$  with a maximum  $1K\Omega$  impedance between  $V_{DDX}$  and  $V_{SS}$ . While in Cold Spare, the device places all outputs into a high impedance state (see DC electrical parameters,  $I_{cs}$ ).

## Logic Diagram



# UT54ACS162245SLV

## Operational Environment <sup>1</sup>

Parameter	Limit	Units
Total Dose	1.0E5	rad(Si)
SEL Latchup	>113	MeV-cm <sup>2</sup> /mg
Neutron Fluence <sup>(Note 2)</sup>	1.0E14	n/cm <sup>2</sup>

**Notes:**

- 1) Logic will not latchup during radiation exposure within the limits defined in the table.
- 2) Not tested, inherent to CMOS technology.

## Absolute Maximum Ratings <sup>1</sup>

Symbol	Parameter	Limit (Mil only)	Units
V <sub>I/O</sub> <sup>(Note 2)</sup>	Voltage any pin	-0.3 to V <sub>DD1</sub> +0.3	V
V <sub>DD1</sub>	Supply voltage	-0.3 to 4.0	V
V <sub>DD2</sub>	Supply voltage	-0.3 to 4.0	V
T <sub>STG</sub>	Storage Temperature range	-65 to +150	°C
T <sub>J</sub> <sup>(Note 3)</sup>	Maximum junction temperature	+150	°C
θ <sub>JC</sub>	Thermal resistance junction to case	20	°C/W
I <sub>I</sub>	DC input current	±10	mA
P <sub>D</sub>	Maximum power dissipation	1	W

**Notes:**

- 1) Stresses outside the listed absolute maximum ratings may cause permanent damage to the device. This is a stress rating only, functional operation of the device at these or any other conditions beyond limits indicated in the operational sections is not recommended. Exposure to absolute maximum rating conditions for extended periods may affect device reliability and performance.
- 2) For Cold Spare mode (V<sub>DD1</sub>=VSS, V<sub>DD2</sub>=VSS), V<sub>I/O</sub> may be -0.3V to the maximum recommended operating level of V<sub>DD1</sub> +0.3V.
- 3) Maximum junction temperature may be increased to +175°C during burn-in and life test.

## Dual Supply Operating Conditions

Symbol	Parameter	Limit	Units
V <sub>DD1</sub>	Supply voltage	2.3 to 3.6	V
V <sub>DD2</sub>	Supply voltage	2.3 to 3.6	V
V <sub>IN</sub>	Input voltage any pin	0 to V <sub>DD1</sub>	V
T <sub>C</sub>	Temperature range	-55 to + 125	°C

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## DC Electrical Characteristics <sup>1</sup>

(-55°C < T<sub>C</sub> < +125°C)

Symbol	Parameter	Condition	MIN	MAX	Unit
V <sub>T+</sub>	Schmitt Trigger, positive going threshold <sup>2</sup>	V <sub>DD</sub> from 2.3 to 3.6		.7V <sub>DD</sub>	V
V <sub>T-</sub>	Schmitt Trigger, negative going threshold <sup>2</sup>	V <sub>DD</sub> from 2.3 to 3.6	.3V <sub>DD</sub>		V
V <sub>H1</sub>	Schmitt Trigger range of hysteresis <sup>9</sup>	V <sub>DD</sub> from 3.0 to 3.6	0.5		V
V <sub>H2</sub>	Schmitt Trigger range of hysteresis <sup>9</sup>	V <sub>DD</sub> from 2.3 to 2.7	0.4		V
I <sub>IN</sub>	Input leakage current <sup>9</sup>	V <sub>DD</sub> from 2.7 to 3.6 V <sub>IN</sub> = V <sub>DD</sub> or V <sub>SS</sub>	-1	3	μA
I <sub>OZ</sub>	Three-state output leakage current <sup>9</sup>	V <sub>DD</sub> from 2.7 to 3.6 V <sub>IN</sub> = V <sub>DD</sub> or V <sub>SS</sub>	-1	3	μA
I <sub>CS</sub>	Cold sparing input leakage current <sup>3, 11</sup>	V <sub>IN</sub> = 3.6 V <sub>DD</sub> = V <sub>SS</sub>	-5	5	μA
I <sub>WS</sub>	Warm sparing input leakage current <sup>3, 11</sup>	V <sub>IN</sub> = V <sub>SS</sub> or V <sub>DD</sub> , V <sub>DD1</sub> = 0, V <sub>DD2</sub> = V <sub>DD</sub> or V <sub>DD1</sub> = V <sub>DD</sub> , V <sub>DD2</sub> = 0	-5	5	μA
I <sub>OS1</sub>	Short-circuit output current <sup>5, 10</sup>	V <sub>O</sub> = V <sub>DD</sub> or V <sub>SS</sub> V <sub>DD</sub> from 3.0 to 3.6	-200	200	mA
I <sub>OS2</sub>	Short-circuit output current <sup>5, 10</sup>	V <sub>O</sub> = V <sub>DD</sub> or V <sub>SS</sub> V <sub>DD</sub> from 2.3 to 2.7	-100	100	mA
V <sub>OL1</sub>	Low-level output voltage <sup>9</sup>	I <sub>OL</sub> = 8mA I <sub>OL</sub> = 100μA V <sub>DD</sub> = 3.0		0.4 0.2	V
V <sub>OL2</sub>	Low-level output voltage <sup>9</sup>	I <sub>OL</sub> = 8mA I <sub>OL</sub> = 100μA V <sub>DD</sub> = 2.3		0.4 0.2	V
V <sub>OH1</sub>	High-level output voltage <sup>9</sup>	I <sub>OH</sub> = -8mA I <sub>OH</sub> = -100μA V <sub>DD</sub> = 3.0	V <sub>DD</sub> - 0.7 V <sub>DD</sub> - 0.2		V
V <sub>OH2</sub>	High-level output voltage <sup>9</sup>	I <sub>OH</sub> = -8mA I <sub>OH</sub> = -100μA V <sub>DD</sub> = 2.3	V <sub>DD</sub> - 0.7 V <sub>DD</sub> - 0.2		V



# UT54ACS162245SLV

## DC Electrical Characteristics <sup>1</sup>

(-55°C < T<sub>c</sub> < +125°C)

Symbol	Parameter	Condition	MIN	MAX	Unit
P <sub>total1</sub>	Power dissipation <sup>4, 6, 7</sup>	C <sub>L</sub> = 40pF V <sub>DD</sub> from 3.0V to 3.6V		6.2	mW/ MHz
P <sub>total2</sub>	Power dissipation <sup>4, 6, 7</sup>	C <sub>L</sub> = 40pF V <sub>DD</sub> from 2.3V to 2.7V		3	MHz
I <sub>DD</sub>	Standby Supply Current V <sub>DD1</sub> or V <sub>DD2</sub>	V <sub>IN</sub> = V <sub>DD</sub> or V <sub>SS</sub> V <sub>DD</sub> = 3.6V			
	Pre-Rad 25°C	$\overline{OE} = V_{DD}$		10	μA
	Pre-Rad -55°C to +125°C	$\overline{OE} = V_{DD}$		475	μA
	Post-Rad 25°C	$\overline{OE} = V_{DD}$		15	mA
C <sub>IN</sub>	Input Capacitance <sup>8</sup>	f = 1MHz @ 0V V <sub>DD</sub> from 2.3V to 3.6V		15	pf
C <sub>out</sub>	Output Capacitance <sup>8</sup>	f = 1MHz @ 0V V <sub>DD</sub> from 2.3V to 3.6V		15	pF
POR	V <sub>DD1</sub> & V <sub>DD2</sub> Power-On <sup>4, 13</sup>	V <sub>DD1</sub> or V <sub>DD2</sub> Zero Volt Offset		250	mV
		V <sub>DD1</sub> and V <sub>DD2</sub> Rise-Time <sup>12</sup>		500	mS

### Notes:

- 1) All specifications valid for radiation dose ≤1E5 rad(Si) per MIL-STD-883, Method 1019.
- 2) Functional tests are conducted in accordance with MIL-STD-883 with the following input test conditions: V<sub>IH</sub> = V<sub>IH</sub>(min) + 20%, - 0%; V<sub>IL</sub> = V<sub>IL</sub>(max) + 0%, - 50%, as specified herein, for TTL, CMOS, or Schmitt compatible inputs. Devices may be tested using any input voltage within the above specified range, but are guaranteed to V<sub>IH</sub>(min) and V<sub>IL</sub>(max).
- 3) All combinations of  $\overline{OE}x$  and DIRx
- 4) Guaranteed by characterization.
- 5) Not more than one output may be shorted at a time for maximum duration of one second.
- 6) Power does not include power contribution of any CMOS output sink current.
- 7) Power dissipation specified per switching output.
- 8) Capacitance measured for initial qualification and when design changes may affect the value. Capacitance is measured between the designated terminal and V<sub>SS</sub> at frequency of 1MHz and a signal amplitude of 50mV rms maximum.
- 9) Guaranteed; tested on a sample of pins per device.
- 10) Supplied as a design limit, but not guaranteed or tested.
- 11) Zero Volts is defined as 0.0 Volts +/- 0.25Volts.
- 12) V<sub>DD1</sub> and V<sub>DD2</sub> Voltage rise is monotonic.
- 13) Rise time measured from V<sub>DD</sub> @ Zero Volts to V<sub>DD</sub> @ greater than 2.3 V.



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## AC Electrical Characteristics <sup>1</sup> (Port B = 3.3 Volt, Port A = 2.5 Volt)

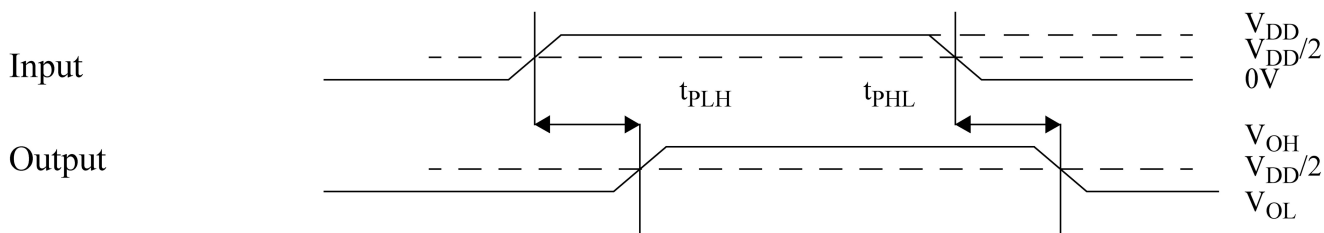
(V<sub>DD1</sub> = 3.0V to 3.6V; V<sub>DD2</sub> = 2.3V to 2.7V, -55°C < T<sub>C</sub> < +125°C)

Symbol	Parameter	Minimum	Maximum	Unit
t <sub>PLH</sub>	Propagation delay Data to Bus	2	10	ns
t <sub>PHL</sub>	Propagation delay Data to Bus	2	10	ns
t <sub>PZL</sub>	Output enable time $\overline{OEx}$ to Bus	2	12	ns
t <sub>PZH</sub>	Output enable time $\overline{OEx}$ to Bus	2	12	ns
t <sub>PLZ</sub>	Output disable time $\overline{OEx}$ to Bus high impedance	2	15	ns
t <sub>PHZ</sub>	Output disable time $\overline{OEx}$ to Bus high impedance	2	15	ns
t <sub>PZL</sub> <sup>2</sup>	Output enable time DIRx to Bus	2	12	ns
t <sub>PZH</sub> <sup>2</sup>	Output enable time DIRx to Bus	2	12	ns
t <sub>PLZ</sub> <sup>2</sup>	Output disable time DIRx to Bus high impedance	2	15	ns
t <sub>PHZ</sub> <sup>2</sup>	Output disable time DIRx to Bus high impedance	2	15	ns
t <sub>SLH</sub> <sup>3</sup>	Skew between outputs (40pF +/- 10 pF on each output)	0	900	ps
t <sub>SHL</sub> <sup>3</sup>	Skew between outputs (40pF +/- 10 pF on each output)	0	900	ps

**Notes:**

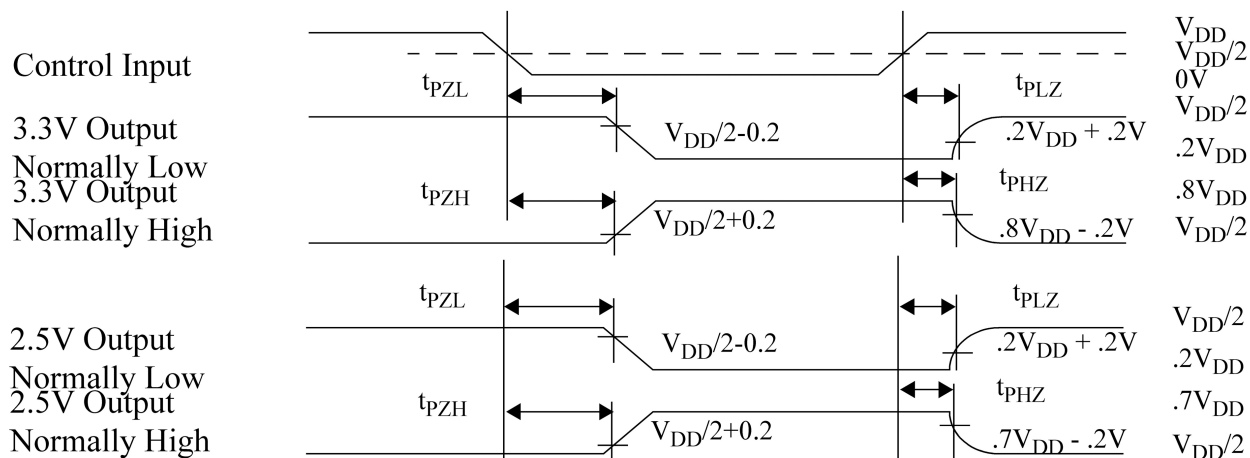
- 1) All specifications valid for radiation dose ≤1E5 rad(Si) per MIL-STD-883, Method 1019.
- 2) DIRx to bus times are guaranteed by design, but not tested.  $\overline{OEx}$  to bus times are tested
- 3) Output skew is defined as a comparison of any two output transitions high-to-low vs. high-to-low and low-to-high vs. low-to-high

### Propagation Delay



# UT54ACS162245SLV

## Enable Disable Times



## AC Electrical Characteristics <sup>1</sup> (Port A = Port B, 3.3 Volt Operation)

(V<sub>DD1</sub> = 3.0 to 3.6V; V<sub>DD2</sub> = 3.0V to 3.6V, -55°C < T<sub>c</sub> < +125°C)

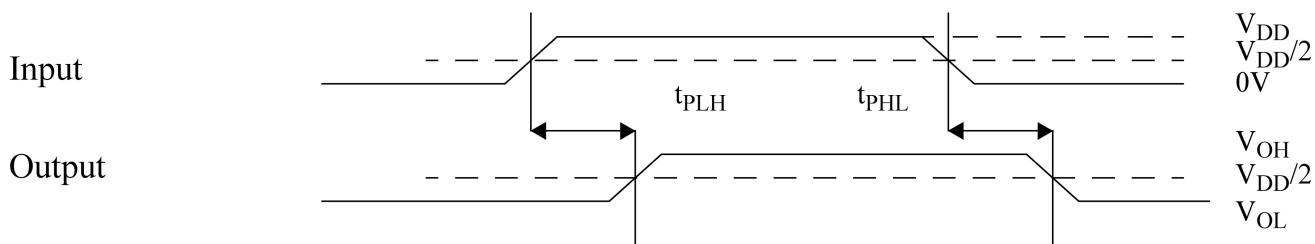
Symbol	Parameter	Minimum	Maximum	Unit
t <sub>PLH</sub>	Propagation delay Data to Bus	2	7.5	ns
t <sub>PHL</sub>	Propagation delay Data to Bus	2	7.5	ns
t <sub>PZL</sub>	Output enable time $\overline{OEx}$ to Bus	2	10	ns
t <sub>PZH</sub>	Output enable time $\overline{OEx}$ to Bus	2	10	ns
t <sub>PLZ</sub>	Output disable time $\overline{OEx}$ to Bus high impedance	2	12	ns
t <sub>PHZ</sub>	Output disable time $\overline{OEx}$ to Bus high impedance	2	12	ns
t <sub>PZL</sub> <sup>2</sup>	Output enable time DIRx to Bus	2	10	ns
t <sub>PZH</sub> <sup>2</sup>	Output enable time DIRx to Bus	2	10	ns
t <sub>PLZ</sub> <sup>2</sup>	Output disable time DIRx to Bus high impedance	2	12	ns
t <sub>PHZ</sub> <sup>2</sup>	Output disable time DIRx to Bus high impedance	2	12	ns
t <sub>SLH</sub> <sup>3</sup>	Skew between outputs (40pF +/- 10 pF on each output)	0	900	ps
t <sub>SHL</sub> <sup>3</sup>	Skew between outputs (40pF +/- 10 pF on each output)	0	900	ps

### Notes:

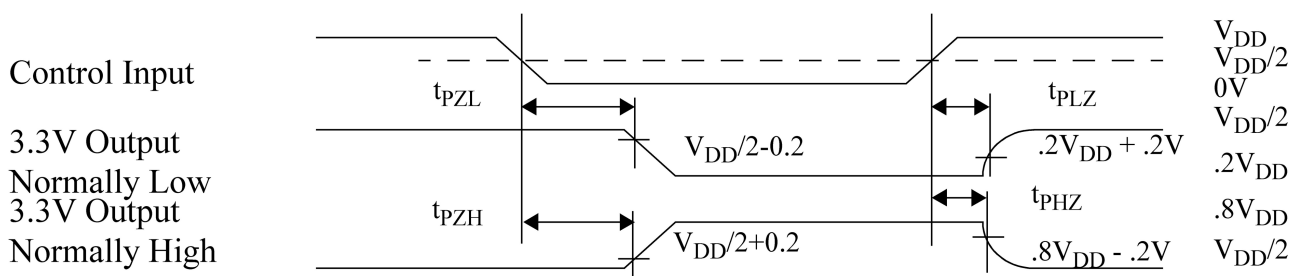
- 1) All specifications valid for radiation dose ≤ 1E5 rad(Si) per MIL-STD-883, Method 1019.
- 2) DIRx to bus times are guaranteed by design, but not tested.  $\overline{OEx}$  to bus times are tested
- 3) Output skew is defined as a comparison of any two output transitions high-to-low vs. high-to-low and low-to-high vs. low-to-high

# UT54ACS162245SLV

## Propagation Delay



## Enable Disable Times



## AC Electrical Characteristics <sup>1</sup> (Port A = Port B, 2.5 Volt Operation)

( $V_{DD1} = 2.3V$  TO  $2.7V$ ;  $V_{DD2} = 2.3V$  to  $2.7V$ ,  $-55^{\circ}C < T_C < +125^{\circ}C$ )

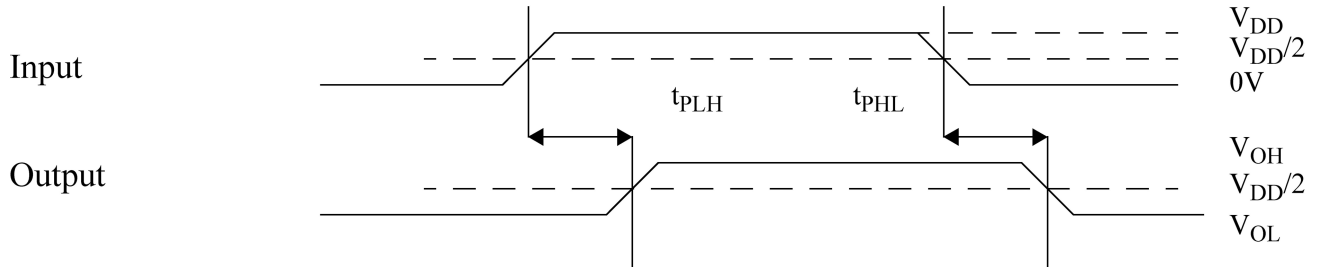
Symbol	Parameter	Minimum	Maximum	Unit
$t_{PLH}$	Propagation delay Data to Bus	2	10	ns
$t_{PHL}$	Propagation delay Data to Bus	2	10	ns
$t_{PZL}$	Output enable time $\overline{OEx}$ to Bus	2	12	ns
$t_{PZH}$	Output enable time $\overline{OEx}$ to Bus	2	12	ns
$t_{PLZ}$	Output disable time $\overline{OEx}$ to Bus high impedance	2	15	ns
$t_{PHZ}$	Output disable time $\overline{OEx}$ to Bus high impedance	2	15	ns
$t_{PZL}^2$	Output enable time DIRx to Bus	2	12	ns
$t_{PZH}^2$	Output enable time DIRx to Bus	2	12	ns
$t_{PLZ}^2$	Output disable time DIRx to Bus high impedance	2	15	ns
$t_{PHZ}^2$	Output disable time DIRx to Bus high impedance	2	15	ns
$t_{SLH}^3$	Skew between outputs (40pF +/- 10 pF on each output)	0	900	ps
$t_{SHL}^3$	Skew between outputs (40pF +/- 10 pF on each output)	0	900	ps

### Notes:

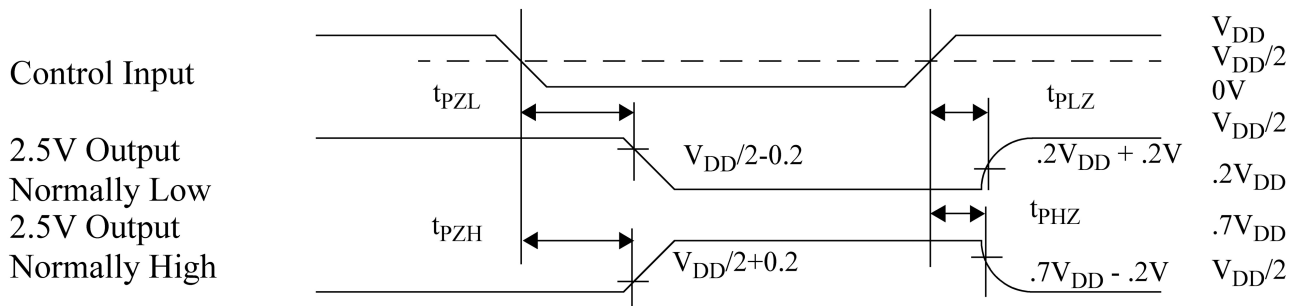
- 1) All specifications valid for radiation dose  $\leq 1E5$  rad(Si) per MIL-STD-883, Method 1019.
- 2) DIRx to bus times are guaranteed by design, but not tested.  $\overline{OEx}$  to bus times are tested
- 3) Output skew is defined as a comparison of any two output transitions high-to-low vs. high-to-low and low-to-high vs. low-to-high

# UT54ACS162245SLV

## Propagation Delay



## Enable Disable Times



# UT54ACS162245SLV

## Package

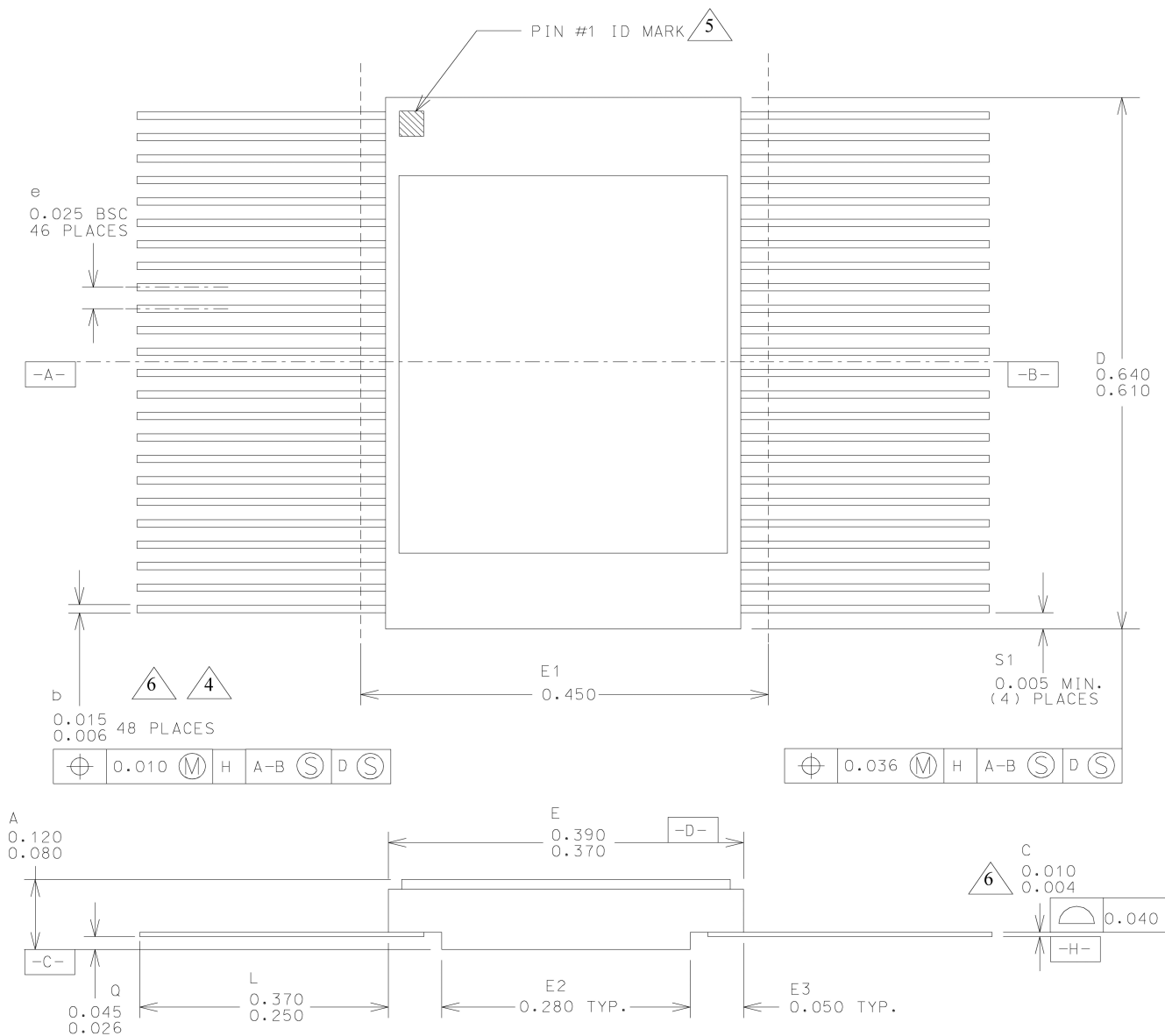


Figure 1. 48-Lead Flatpack

### Notes:

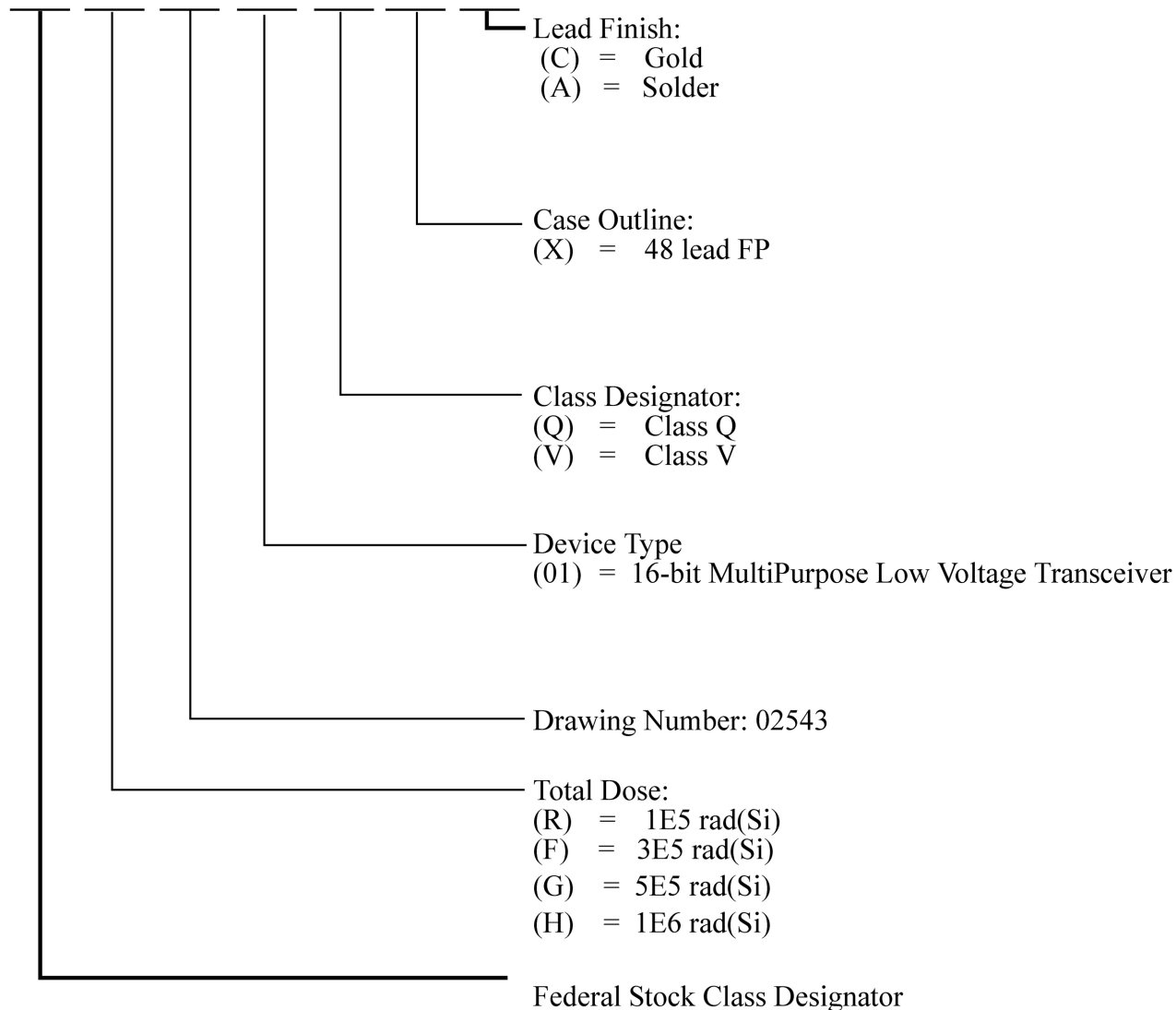
- 1) All exposed metalized areas are gold plated over electroplated nickel per MIL-PRF-38535.
- 2) The lid is electrically connected to VSS.
- 3) Lead finishes are in accordance with MIL-PRF-38535.
- 4) Lead position and colanarity are not measured.
- 5) ID mark symbol is vendor option.
- 6) With solder, increase maximum by 0.003.

# UT54ACS162245SLV

## Ordering Information

### UT54ACS162245SLV: SMD

5962 R 02543 01 \* \* \*

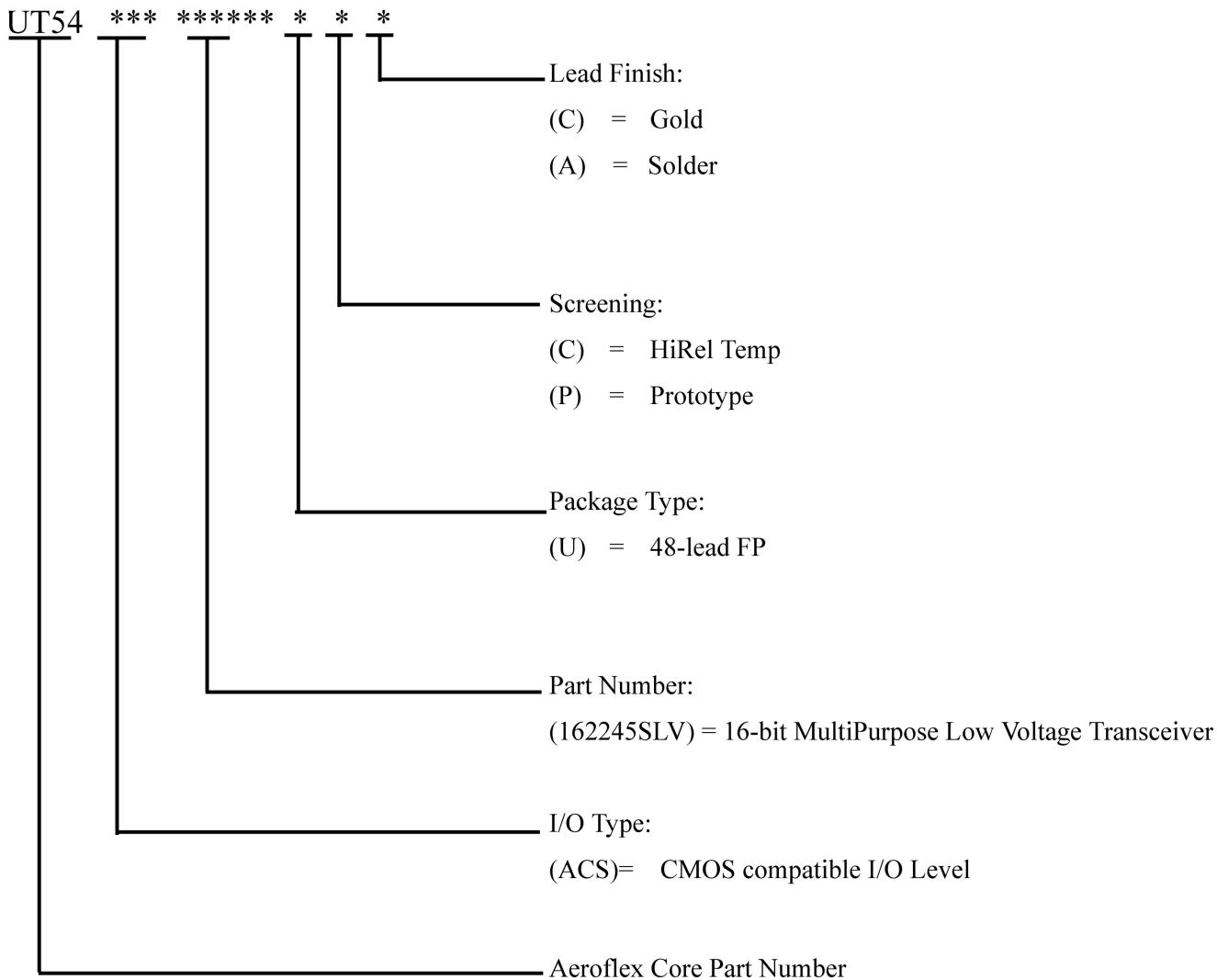


**Note:**

1) Total dose radiation must be specified when ordering. QML Q and QML V not available without radiation hardening.

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## UT54ACS162245SLV



**Notes:**

- 1) HiRel Temperature Range flow per CAES Colorado Springs Manufacturing Flows Document. Devices are tested -55C, room temp, and 125C. Radiation neither tested nor guaranteed.
- 2) Prototype flow per CAES Colorado Springs Manufacturing Flows Document Tested at 25C only. Lead finish is gold only. Radiation neither tested nor guaranteed.



# UT54ACS162245SLV

## Datasheet Definitions

	DEFINITION
Advanced Datasheet	CAES reserves the right to make changes to any products and services described herein at any time without notice. The product is still in the development stage and the datasheet <b>is subject to change</b> . Specifications can be <b>TBD</b> and the part package and pinout are <b>not final</b> .
Preliminary Datasheet	CAES reserves the right to make changes to any products and services described herein at any time without notice. The product is in the characterization stage and prototypes are available.
Datasheet	Product is in production and any changes to the product and services described herein will follow a formal customer notification process for form, fit or function changes.

The following United States (U.S.) Department of Commerce statement shall be applicable if these commodities, technology, or software are exported from the U.S.: These commodities, technology, or software were exported from the United States in accordance with the Export Administration Regulations. Diversion contrary to U.S. law is prohibited.

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